

JC20 Rec'd PCT/PTO 03 OCT 2005

PTO/SB/08a/b (08-03)

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Substitute for form 1449A/B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(Use as many sheets as necessary)</i>		<b>Complete if Known</b>	
		Application Number	Not Yet Assigned
		Filing Date	Concurrently Herewith 10/03/2005
		First Named Inventor	Tomohiro Kawase
		Art Unit	NA- 1792
		Examiner Name	Not Yet Assigned Hiteshew
Sheet 1 of 2	Attorney Docket Number	20239/0202145-USO	

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
	AA*	US-5,647,917-A	07-15-1997	Sumitomo Electric Industries, Ltd.	Olda ETAL.

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				
	BA	JP-03-237088-A	10-22-1991	Nippon Mining Co Ltd	Abstract only	✓
	BB	JP-2000-313699-A	11-14-2000	Japan Energy Corp	Abstract only	✓
	BC	JP-03-040987-A	02-21-1991	Nippon Telegr & Teleph Corp <NTT>	Abstract only	✓
	BD	JP-08-078348-A	03-22-1996	Sumitomo Electric Ind Ltd	Abstract only	✓
	BE	JP-11-302094-A	11-02-1999	Japan Energy Corp	Abstract only	✓

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	CA	International Search Report for PCT/JP2004/006427 mailed October 5, 2004	
	CB	P. RUDOLPH, et al., Studies on interface curvature during vertical Bridgman growth of InP in a flat-bottom container, Journal of Crystal Growth, 1996, Vol. 158, pp 43-48	
	CC	esp@cenet document view: Abstract of EP 0701008 published on March 13, 1996	
	CD	XIAOYU HU, et al., Three Inch VGF Semi-insulating InP, Post Deadline Papers, Tenth International Conference on Indium Phosphide and Related Materials (IPRM '98), May 11-15, 1998, pp. 15-16	
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	CF	T. ASAH, et al., Growth of 100mm Diameter <100> InP Single Crystals by the Vertical Gradient Freezing Method, Post Deadline Papers, Tenth International Conference on Indium Phosphide and Related Materials (IPRM '98), May 11-15, 1998, pp. 1-2	
	CG	TOSHIKAKI ASAH, et al., Growth of 100-mm-Diameter <100> InP Single Crystals by the Vertical Gradient Freezing Method, Jpn. J. Appl. Phys. Vol. 38, February, 1999, pp. 977-980	
	CH	T. ASAH, et al., VGF CRYSTAL GROWTH AND VAPOR-PHASE Fe DOPING TECHNOLOGIES FOR SEMI-INSULATING 100mm DIAMETER InP SUBSTRATES, 11th International Conference on Indium Phosphide and Related Materials, May 16-20, 1999, pp. 249-254	
	CI	FUMIO MATSUMOTO, et al., Growth of twin-free <100> InP single crystals by the liquid encapsulated vertical Bridgman technique, Journal of Crystal Growth 132, 1998, pp. 348-350	
	CJ	E.M. MONBERG, et al., THE DYNAMIC GRADIENT FREEZE GROWTH OF InP, Journal of Crystal Growth 94, 1989, pp. 109-114	

Examiner Signature	/Felisa Hiteshew/	Date Considered	03/20/2008
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ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /F.H./